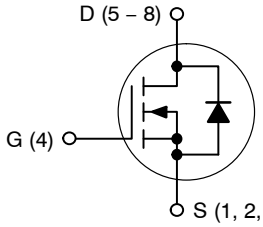
MOSFET – Power, Single N-Channel
40 V, 7.3 mΩ, 51 A

NVTFS5C466NL

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
40 V	7.3 mΩ @ 10 V	51 A
	12 mΩ @ 4.5 V	

Features
- Small Footprint (3.3 x 3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- NVTFS5C466NLWF – Wettable Flanks Product
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

N-CHANNEL



MAXIMUM RATINGS (T_J = 25 °C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	40	V
Gate-to-Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3, 4)	Steady State	T_C = 25 °C	I_D	51	A
		T_C = 100 °C		36	
Power Dissipation $R_{\theta JC}$ (Notes 1, 2, 3)		T_C = 25 °C	P_D	38	W
		T_C = 100 °C		19	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)	Steady State	T_A = 25 °C	I_D	14	A
		T_A = 100 °C		12	
Power Dissipation $R_{\theta JA}$ (Notes 1, 3)		T_A = 25 °C	P_D	3.1	W
		T_A = 100 °C		1.5	
Pulsed Drain Current	T_A = 25 °C, t_p = 10 μs		I_{DM}	214	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	31.3	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)}$ = 3 A)			E_{AS}	72	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

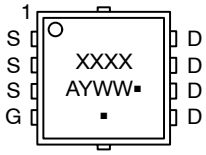
Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 3)	$R_{\theta JC}$	4.0	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	48	

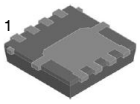
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface-mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

MARKING DIAGRAMS

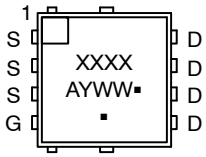


WDFN8
(μ8FL)
CASE 511AB





WDFNW8
CASE 515AQ



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION
See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}$/T_J			29		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 40 V, T_J = 25 °C			10	μA
		V_{GS} = 0 V, V_{DS} = 40 V, T_J = 125 °C			250	
Gate-to-Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V			100	nA
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 30 μA	1.2		2.2	V
Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 10 A		6.1	7.3	mΩ
		V_{GS} = 4.5 V, I_D = 10 A		9.7	12	
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 25 A		33		S
CHARGES AND CAPACITANCES						
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 25 V		880		pF
Output Capacitance	C_{oss}			340		
Reverse Transfer Capacitance	C_{rss}			16		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 32 V, I_D = 25 A		7.0		nC
Threshold Gate Charge	$Q_{G(TH)}$			1.8		nC
Gate-to-Source Charge	Q_{GS}			3.3		
Gate-to-Drain Charge	Q_{GD}			2.5		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 32 V, I_D = 25 A		16		nC
SWITCHING CHARACTERISTICS (Note 6)						
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 4.5 V, V_{DS} = 32 V, I_D = 25 A, R_G = 2.5 Ω		10		ns
Rise Time	t_r			67		
Turn-Off Delay Time	$t_{d(off)}$			26		
Fall Time	t_f			32		
DRAIN-SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 20 A, T_J = 25 °C		0.9	1.2	V
		V_{GS} = 0 V, I_S = 20 A, T_J = 125 °C		0.8		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 25 A		22		ns
Charge Time	t_a			10		
Discharge Time	t_b			12		
Reverse Recovery Charge	Q_{RR}			6.0		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

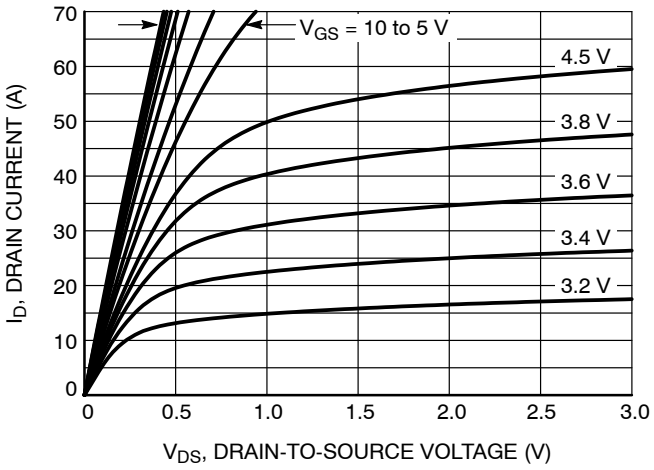


Figure 1. On-Region Characteristics

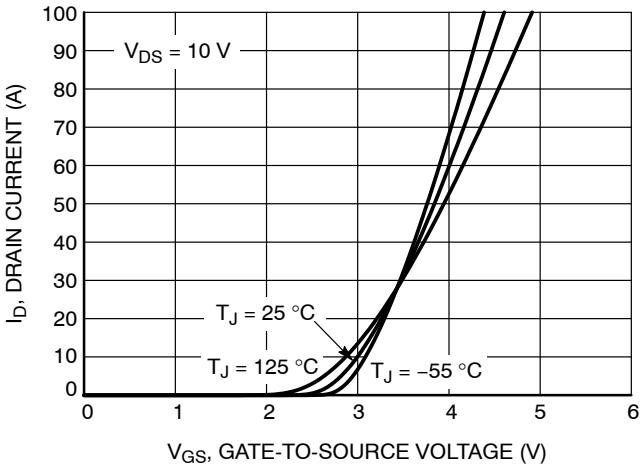


Figure 2. Transfer Characteristics

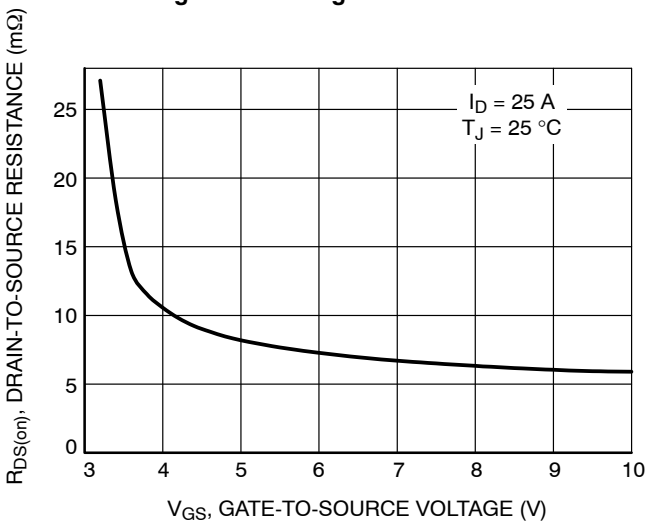


Figure 3. On-Resistance vs. Gate-to-Source Voltage

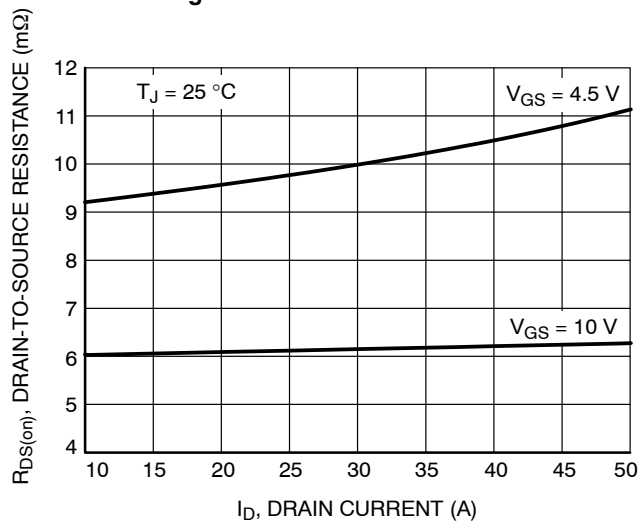


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

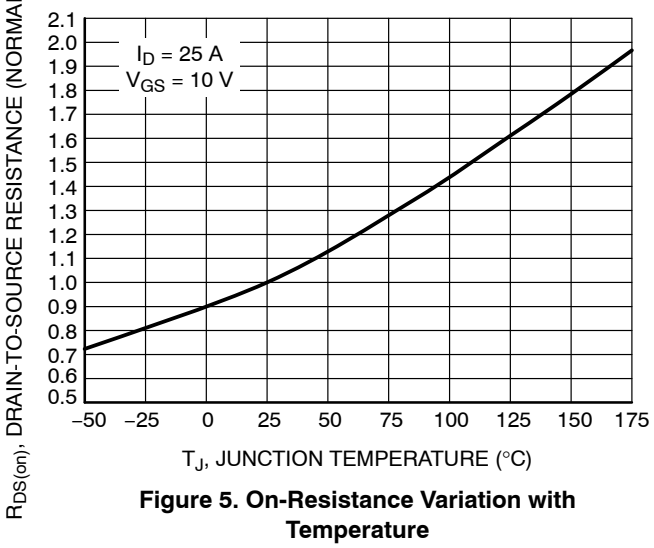


Figure 5. On-Resistance Variation with Temperature

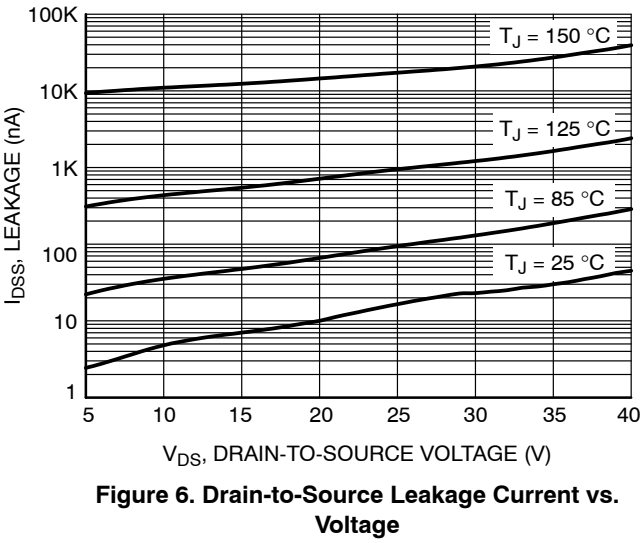


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

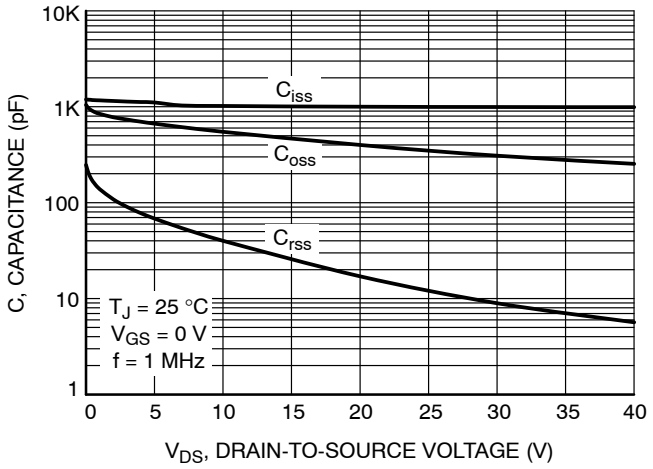


Figure 7. Capacitance Variation

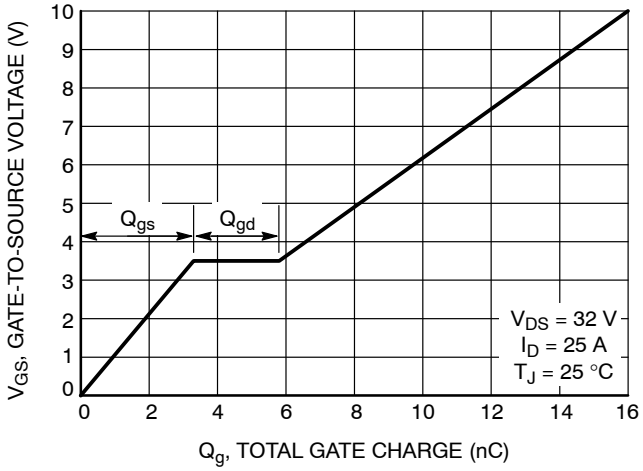


Figure 8. Gate-to-Source vs. Total Charge

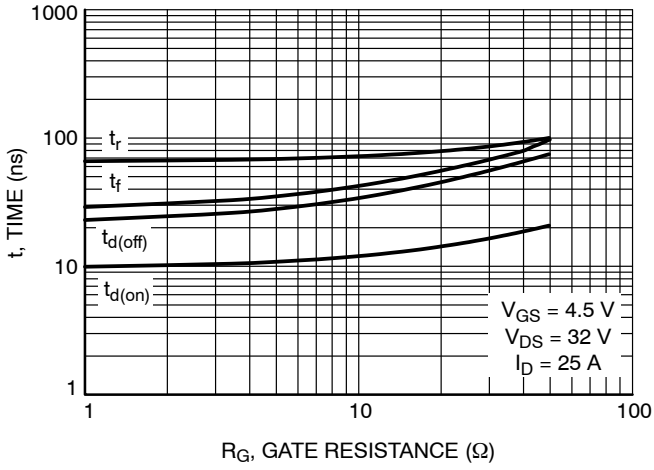


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

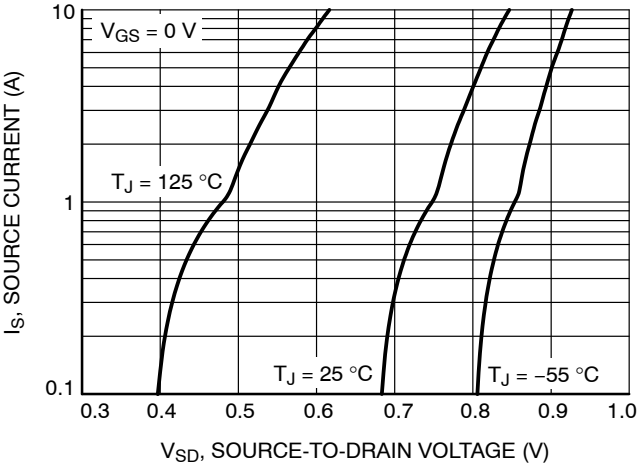


Figure 10. Diode Forward Voltage vs. Current

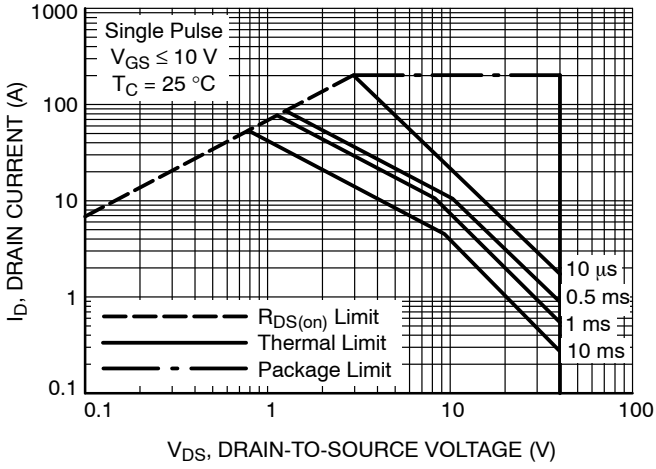


Figure 11. Maximum Rated Forward Biased Safe Operating Area

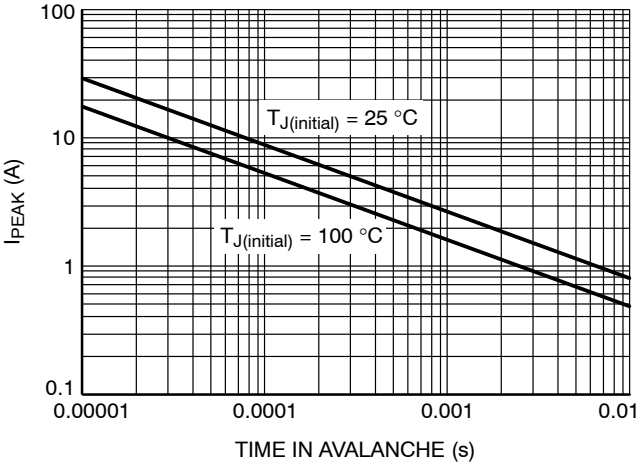


Figure 12. Maximum Drain Current vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

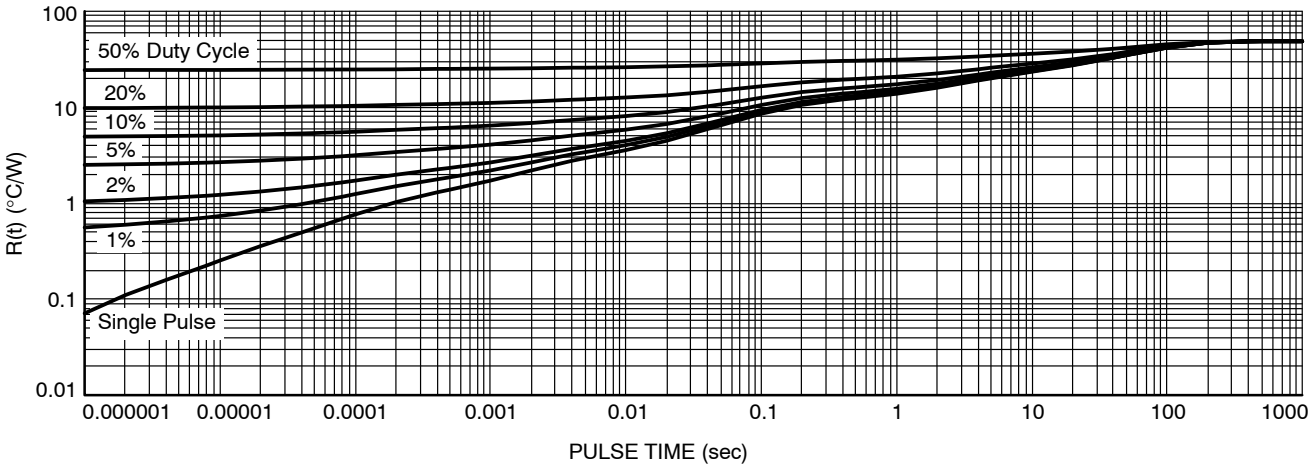


Figure 13. Thermal Response

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DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping†
NVTFS5C466NLTAG	466L	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS5C466NLETAG	466L	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS5C466NLTWG	466L	WDFN8 (Pb-Free)	5000 / Tape & Reel
NVTFS5C466NLWFTAG	66LW	WDFNW8 (Pb-Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

REVISION HISTORY

Revision	Description of Changes	Date
7	Add 515AQ package option and new ordering information	5/12/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

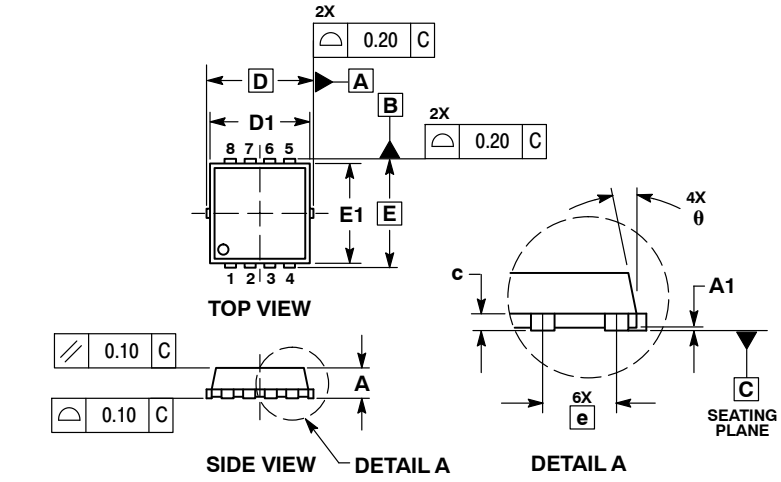
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SCALE 2:1

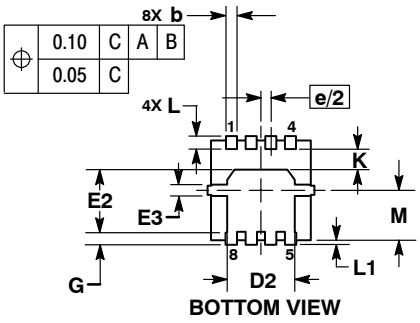
WDFN8 3.3x3.3, 0.65P
CASE 511AB
ISSUE D

DATE 23 APR 2012



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30 BSC			0.130 BSC		
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30 BSC			0.130 BSC		
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e	0.65 BSC			0.026 BSC		
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0 °	---	12 °	0 °	---	12 °



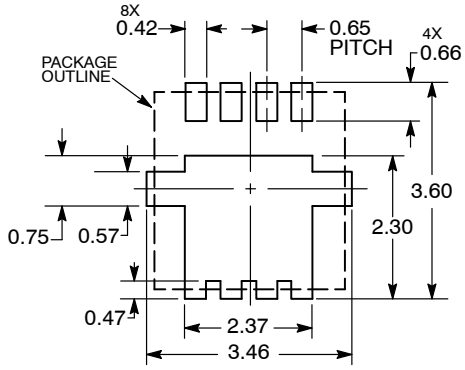
GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



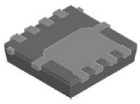
DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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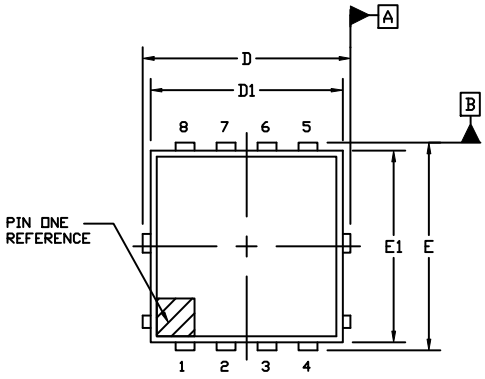
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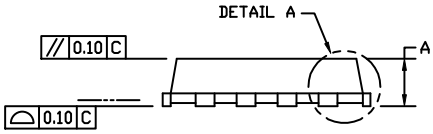


WDFNW8 3.3x3.3, 0.65P
CASE 515AQ
ISSUE O

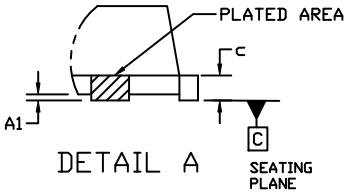
DATE 30 APR 2021



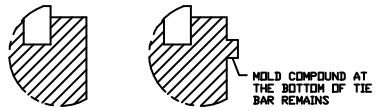
TOP VIEW



SIDE VIEW



DETAIL A



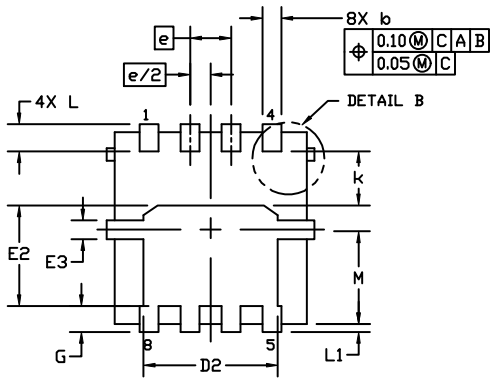
DETAIL B
ALTERNATE CONSTRUCTION

DETAIL B

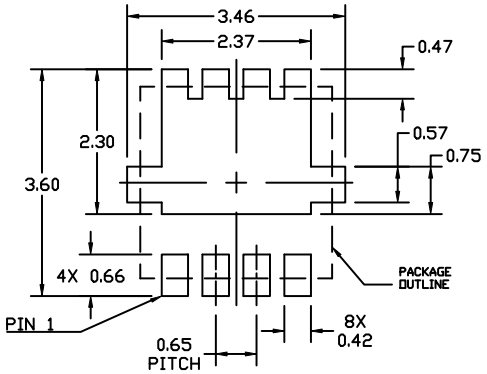
NOTES:

1. DIMENSIONING AND TOLERANCING PER.ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	----	0.05
b	0.23	0.30	0.40
c	0.15	0.20	0.25
D	3.05	3.30	3.55
D1	2.95	3.05	3.15
D2	1.98	2.11	2.24
E	3.05	3.30	3.55
E1	2.95	3.05	3.15
E2	1.47	1.60	1.73
E3	0.23	0.30	0.40
e	0.65 BSC		
G	0.30	0.41	0.51
K	0.65	0.80	0.95
L	0.30	0.43	0.59
L1	0.06	0.13	0.20
M	1.40	1.50	1.60



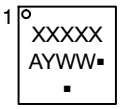
BOTTOM VIEW



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
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▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**WDFNW8 3.3X3.3, 0.65P**		**PAGE 1 OF 1**

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